



# Future of Low Mass Pixel Systems with MAPS

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- Specifications for different experiments
- MAPS, standard performances & challenges
- 2D or planar CMOS technologies
- Integration technologies
- 3D integrated circuit technologies
- Conclusion

# Why low mass + high granularity ?

## ■ Charm hadrons

x STAR, ALICE, CBM

## ■ Charm jet tagging

x ILC, CLIC, (superB)

## ■ B decay length

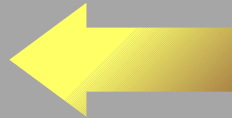
x SuperB

## ■ Beam background

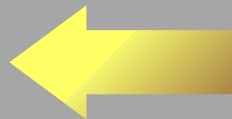
x ILC, CLIC, SuperB, CBM

## ■ Low momentum tracks

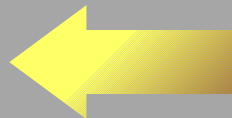
x STAR, ALICE



Charm hadrons  $c\tau \sim 100 \mu\text{m}$



Low  $\beta\gamma_B \sim 0.28 \rightarrow \sigma(\Delta z) \sim 60 \mu\text{m}$



$P_{\perp}$  down to 100 MeV/c

Impact parameter resolution:  
(2 layers hypothesis)


$$\sigma_{I.P.} \approx \sigma_{sing.pt.} \frac{\sqrt{r_1^2 + r_2^2}}{r_2 - r_1} \circ \frac{\sqrt{x/X_0} r_1}{p \sin^{3/2} \theta} \times cst$$

# Specification summary

## ■ For the most demanding layer ( 1<sup>st</sup> out of 2 to 6)

- ✘ Orders of magnitude, no security factor, subject to modification
- ✘ Apply to one layer only

	STAR	CBM	ALICE	ILC 500GeV	CLIC 3TeV	SuperB
spatial resolution ( $\mu\text{m}$ )	< 10	~5	~ 5	< 3	~ILC	~15
Material budget (% X0)	< 0.3	0.3	0.3	< 0.3	~ILC	<1.0
Hit rate ( $\times 10^6/\text{s}/\text{cm}^2$ )	$O(0.1)$	$O(1-10)$	$O(1)$	$O(0.2)$	$O(1)$	$O(20)$
Radiation / year (Mrad) ( $n_{\text{eq}}/\text{cm}^2$ )	$O(0.2)$ $O(10^{12})$	$O(30)$ $< 10^{14}$		$O(0.1)$ $O(10^{11})$	x10/ ILC	$O(3)$ ?
Power dissipation ( $\text{W}/\text{cm}^2$ )	0.1	1-2		0.1		1-5

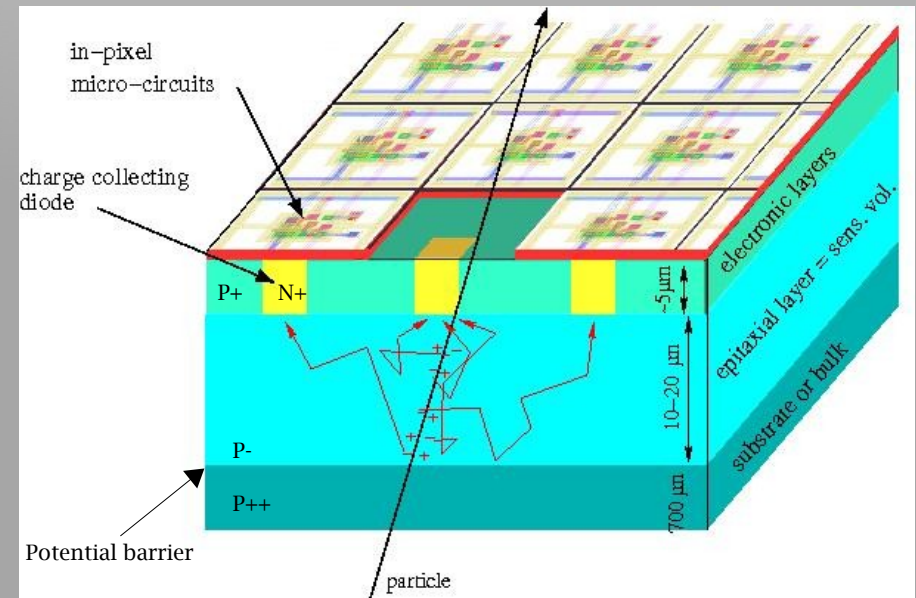
Notes:  $10^6$  hits/s/cm<sup>2</sup> over 20x20  $\mu\text{m}^2$  pixels  0.04% occupancy @ 100  $\mu\text{s}$  readout  
BUT sparse data ~70 Mbits/s over 1 cm<sup>2</sup>

ILC, CBM r.o. time ~10 $\mu\text{s}$  / CLIC timestamp ~10ns

# MAPS, the basics

## ■ Technology

- ✗ Industry standard for ICs
- ✗ All processes not optimized
  - Epitaxial layer thickness
  - # metal layers
  - Nwell – Psubstrate junction



## ■ Intrinsically thin sensors

- ✗ sensitive layer ~10-20 μm
  - Small MIP signal, few 100 e- per pixel → **requires low pixel noise  $O(10 e^-)$**
- ✗ Substrate almost useless
  - Few μm enough, total thickness could reach 20 μm
- ✗ Monolithic & active
  - No external IC required in vicinity

# MAPS, standard performances

## ■ From the MIMOSA family

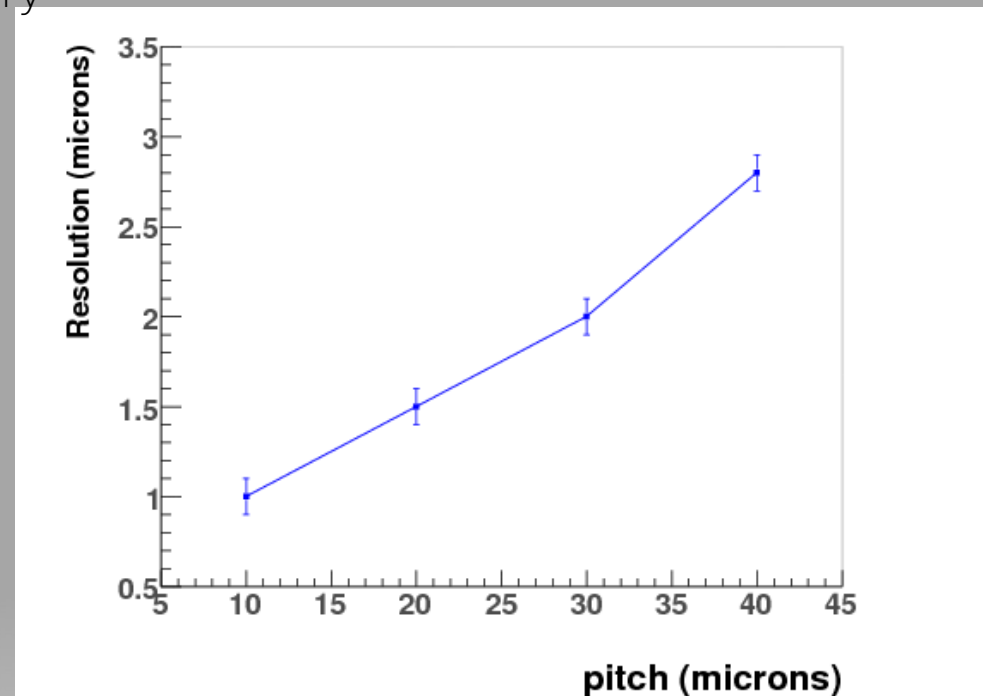
- x Developed at IPHC-Strasbourg
- x AMS 0.35  $\mu\text{m}$  process,  $\sim 11 \mu\text{m}$  epitaxial layer
- x 3 transistors pixel - Sequential analogue readout
- x Performances assessed also @ 50  $\mu\text{m}$  thickness
  - Thinning routinely achieve by industry

## ■ Hit rate

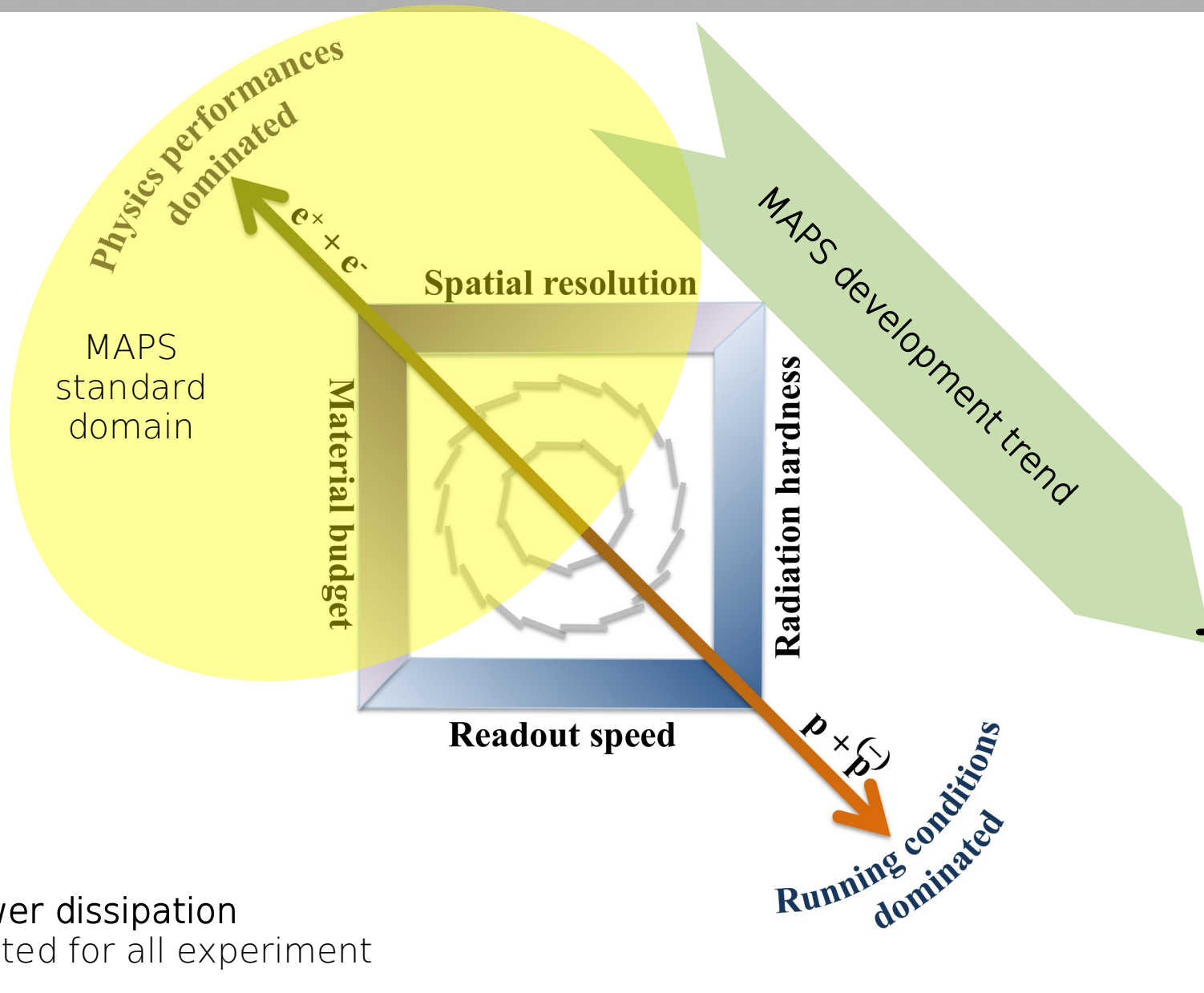
- x With parallel analog outputs
- x 1Mpixels  $\sim 1\text{ms}$  r.o, time

## ■ Radiation tolerance

- x Ionizing:  $\sim \text{Mrad}$
- x Non-ionizing: few  $10^{12} n_{\text{eq}}/\text{cm}^2$
- x Integration time and temperature dependant



# Maps, the challenges



- 2D process
- Integration tech.
- 3D process



# 2D (planar) process

## ■ Increasing the hit rate

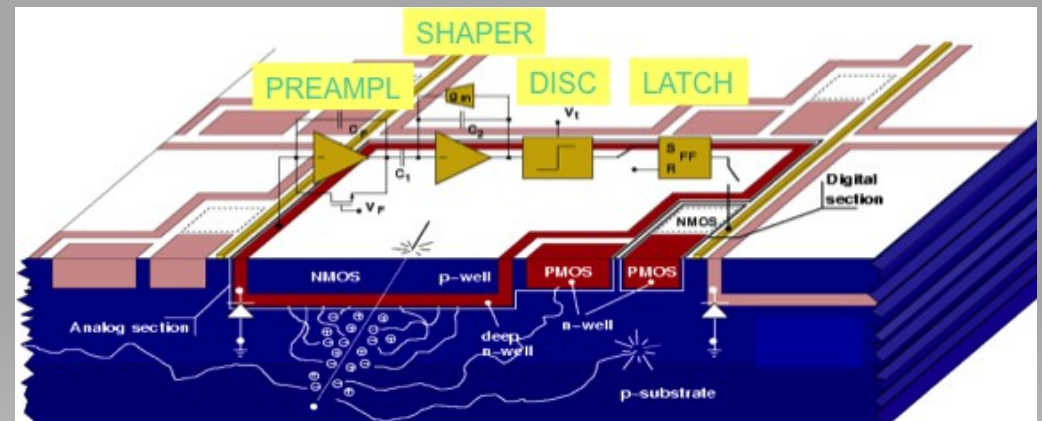
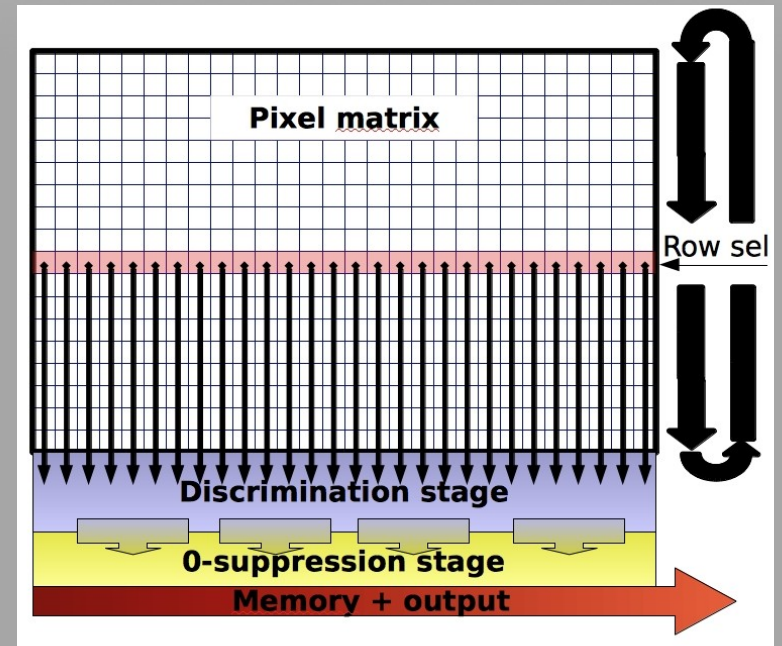
- x Basic idea: zero-suppression

## ■ Strategy 1:

- x **Peripheral discrimination**
- x Increasing the readout speed
- x IPHC(Strasbourg)+IRFU(Saclay) groups

## ■ Strategy 2:

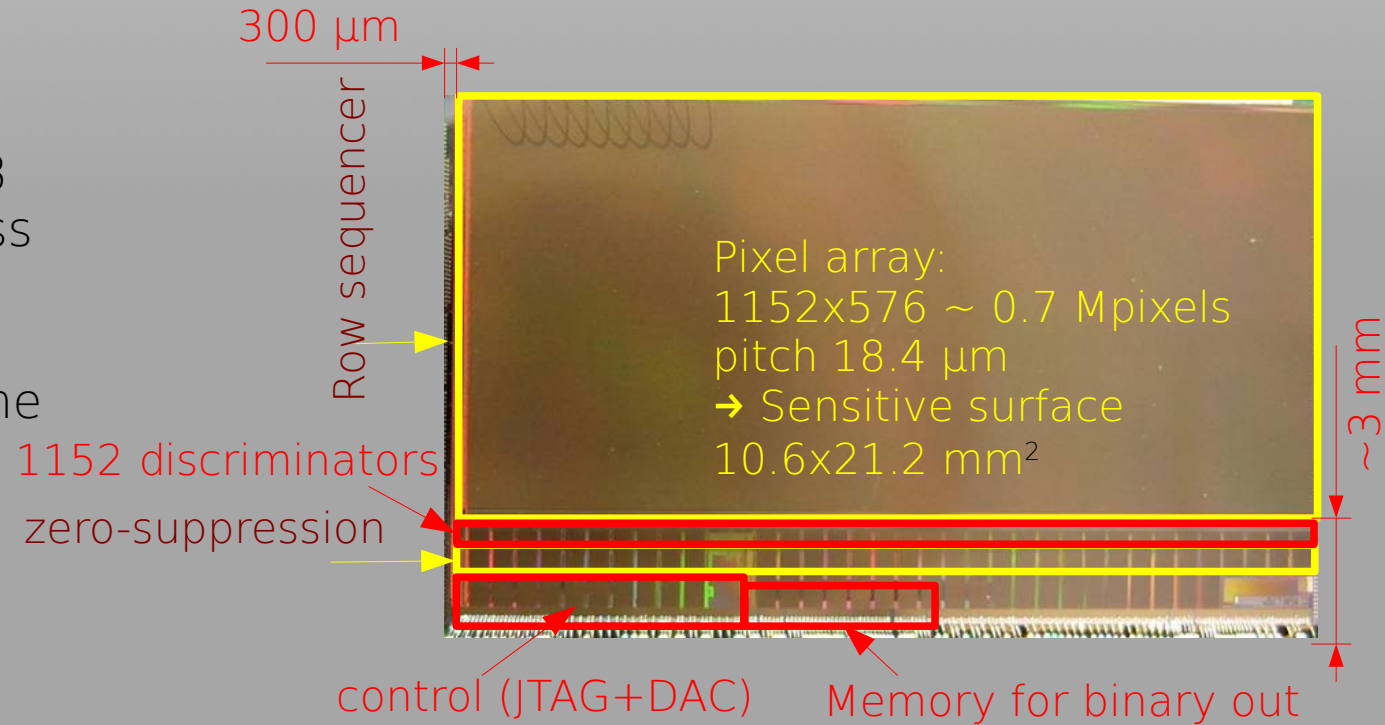
- x **In-pixel discrimination**
- x Data-driven r.o. mode with time-stamp @ periphery
- x SLIM5 collaboration (INFN+Italian Universities)
- x Also INMAPS process @ RAL



# 2D – peripheral discrimination

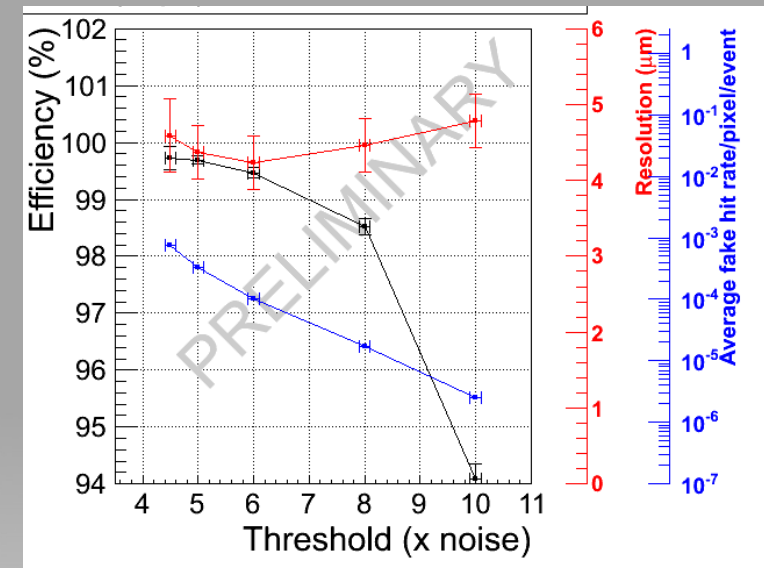
## ■ MIMOSA 26

- x Fabricated end 2008  
AMS 0.35  $\mu\text{m}$  process
- x Binary output
- x  $\sim 100$   $\mu\text{s}$  readout time
- x  $> 10^6$  hits/cm<sup>2</sup>/s



## ■ First applications

- x EUDET beam telescope  
(running since 2009)
- x FIRST experiment  
(2011, GSI)
- x Forerunner of final sensor for STAR (2013)
  - Talk by M. Szelezniak  
"MAPS based vertex detector at STAR",  
Thursday 17h30





# 2D – peripheral discrimination

## ■ Further applications, r.o. Time $\sim 10 \mu\text{s}$

x ILC, CBM

→ [Talk C.Schmidt](#) "FAIR Silicon Tracking Detector System", Thursday 17h

## ■ Extrapolate MIMOSA26 architecture

x Move to  $0.18 \mu\text{m}$  process (ex. INMAPS techno. introduced by RAL)

→ Higher internal clock

→ Lower power dissipation

→ Reduced insensitive area

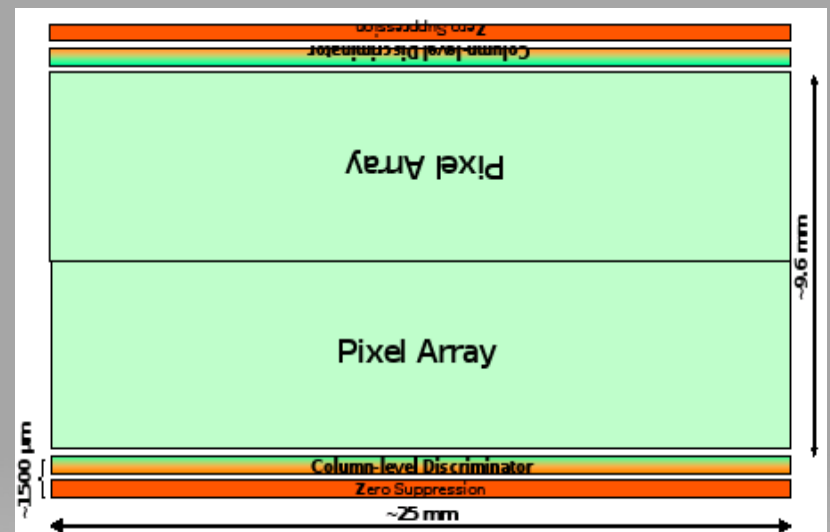
x Double-sided readout

→ readout time / 2

x Stretched pixels with ADC

→ Similar spatial resolution

→ Readout time / 4-5

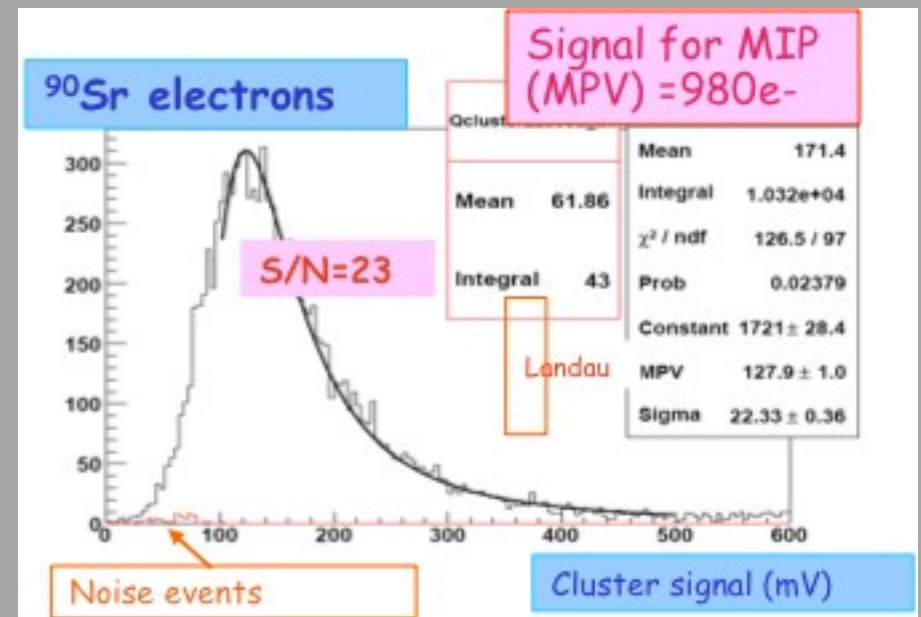
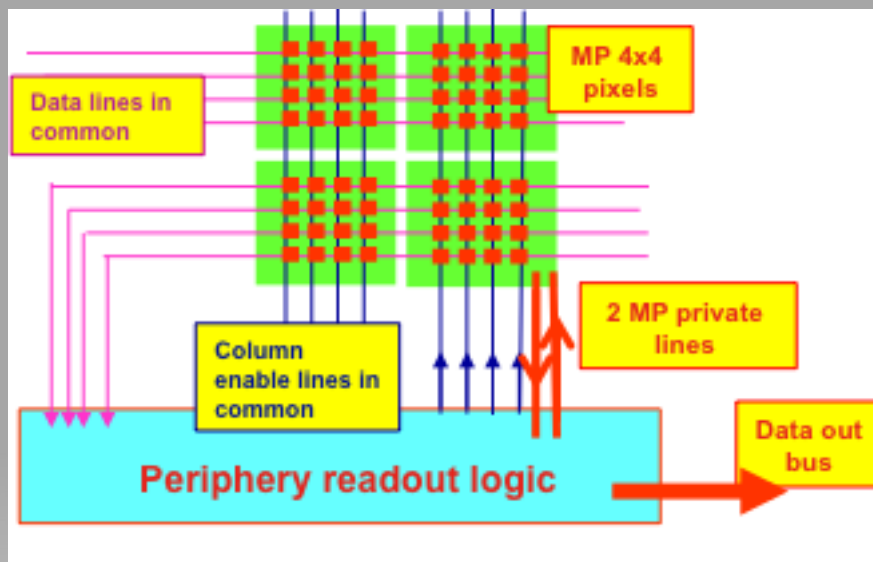
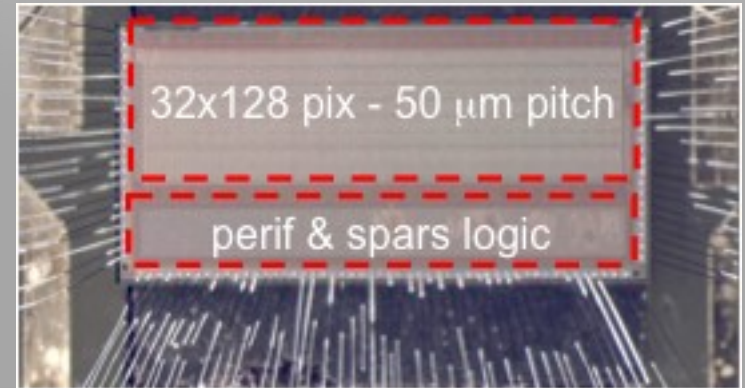


# 2D - In-Pixel discrimination

## ■ APSEL family

- x Techno. STM .13  $\mu\text{m}$ ,
- x APSEL4D  $\rightarrow$  APSEL5T
  - $\rightarrow$  Pixel  $50 \times 50 \mu\text{m}^2 \rightarrow 40 \times 40 \mu\text{m}^2$
  - $\rightarrow$  Amplification scheme "smaller"
- x Read-out through MacroPixel
  - $\rightarrow$  Using dedicated logic
  - $\rightarrow$  Optimized for  $100 \cdot 10^6$  hits/ $\text{cm}^2/\text{s}$

APSEL 4D, fab. Early 2008



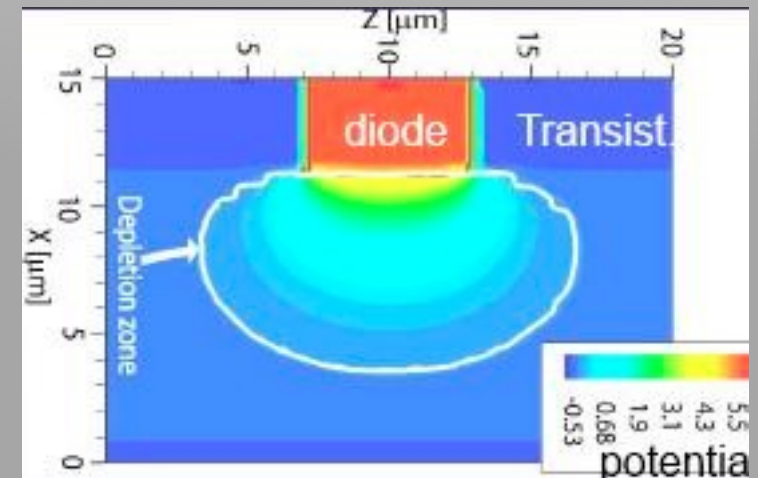
# (non-ionizing) Radiation hard 2D process

## ■ High resistivity epitaxial layer

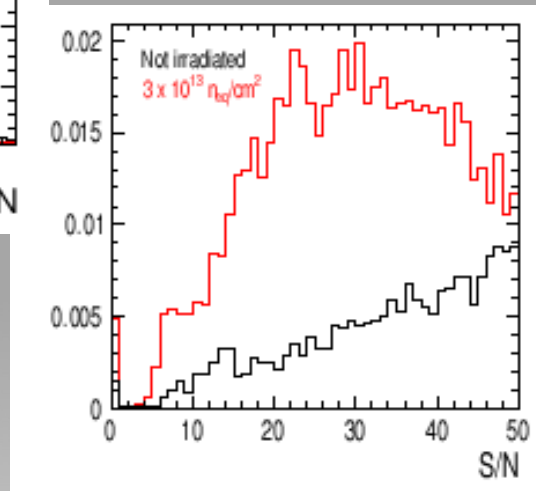
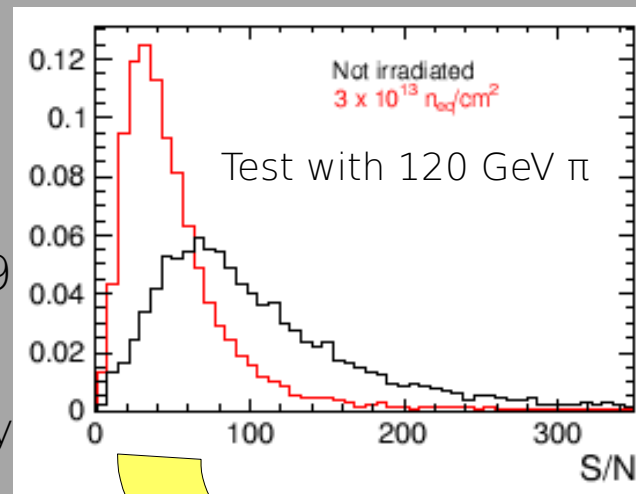
- x Allow some level of depletion
- x Faster collection
  - lower sensitivity to crystal defects
  - lower signal spread over pixels

## ■ Prototypes @ IPHC

- x MIMOSA 25, fab 2008
  - XFAB 0.6  $\mu\text{m}$ , 1000  $\Omega\cdot\text{cm}$
  - 20  $\mu\text{m}$  pitch
  - 80  $\mu\text{s}$  analog read-out
- x MIMOSA 26HR, fab end 2009
  - AMS 0.35  $\mu\text{m}$ , 400  $\Omega\cdot\text{cm}$
  - 10, 15 & 20  $\mu\text{m}$  epitaxial lay
  - In beam test, up to  $3 \cdot 10^{13} n_{\text{eq}}/\text{cm}^2$
- x Also provided by INMAPS process (RAL) & IBM LePIX (CERN)



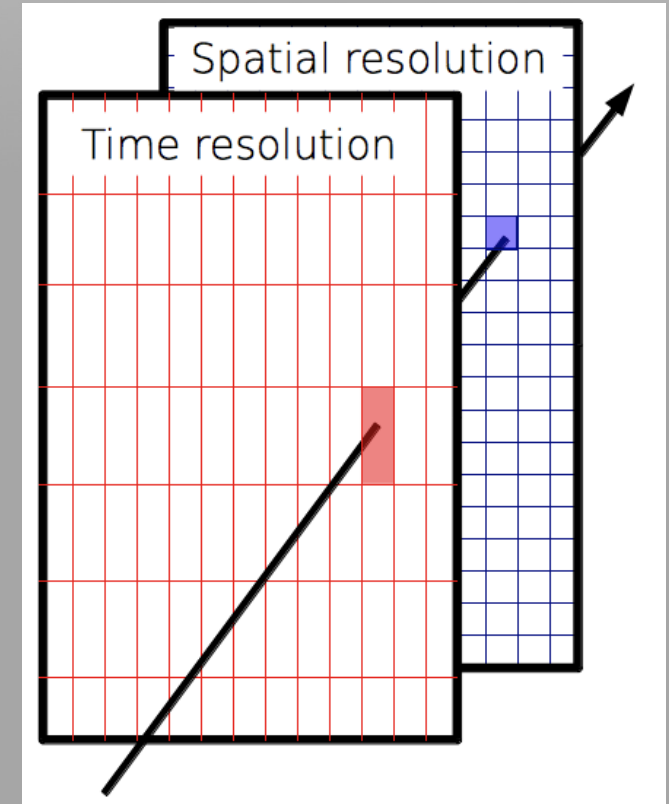
TCAD simulation by A.Dorokhov IPHC



# Integration technologies

## ■ “Smarter” AND still thin

- x Basic idea: **multi-points in a single layer**
- x Possible with
  - Thin sensors
  - Thin support material
  - thin cables
- x **Benefits**
  - Tracklets for pointing res. or triggering
  - Mixing  $\neq$  granularity/speed compromises



## ■ MAPS advantages

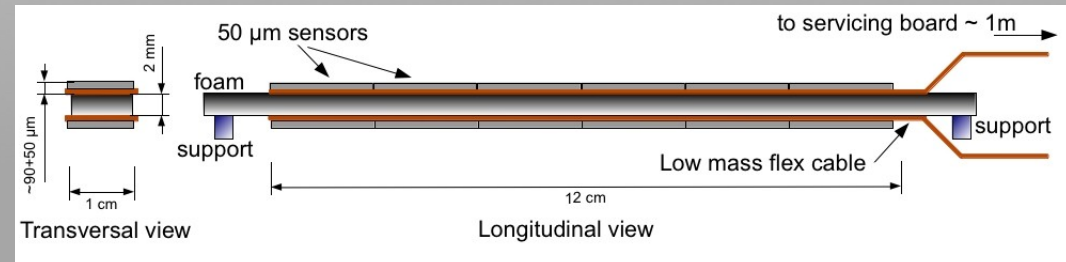
- x Already thin
- x No additional IC required
- x  $\sim 30^{\circ}\text{C}$  operation possible
  - Active cooling avoidable

# Double sided ladders

## ■ The PLUME project



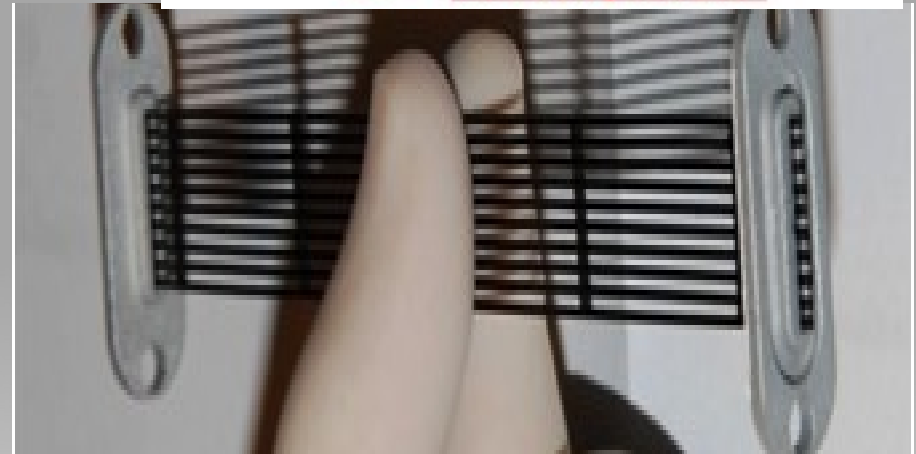
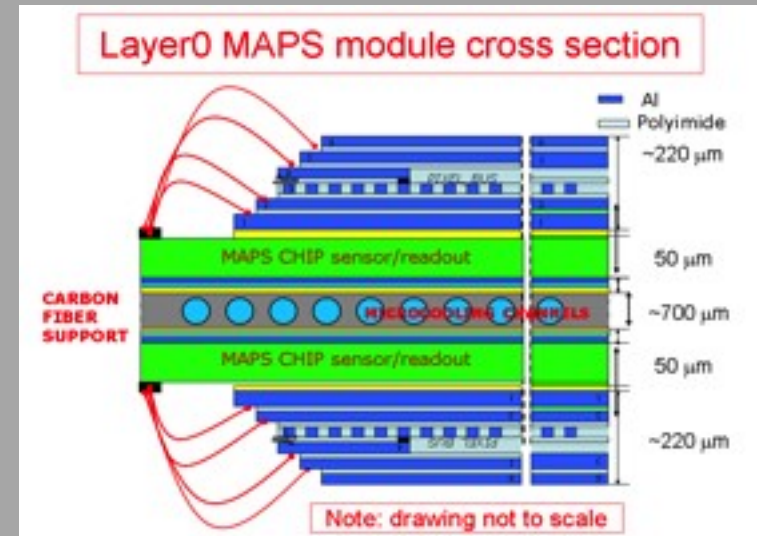
- x Double sided ladder @ 0.4% X0
- x Passive cooling: air flow
- x Power pulsing
- x Bristol U., DESY, Oxford U., IPHC
- x Several iterations over 2009-2012
  - Current proto @ 0.6%X0



## ■ The SuperB project



- x Few W/cm<sup>2</sup> → Active cooling required
- x Support from carbon fiber μtubes
  - 0.15%X0
- x INFN and Italian Universities groups



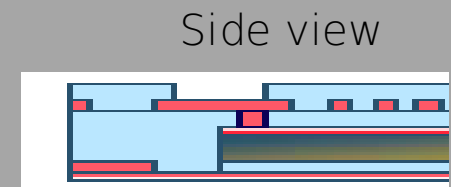
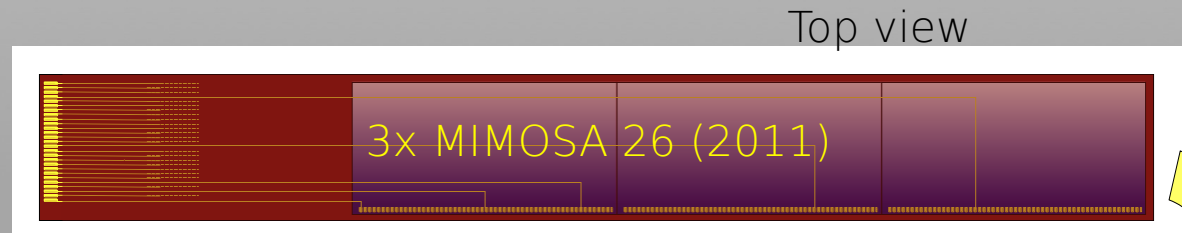
# From integration to embedding

## ■ The SERWIETE project

- x Embed sensors inside **soft polyimide cable**
  - Cable with traces  $\sim < 0.1\%$  X0
- x Benefit fully from the MAPS thinness
  - **Sensors  $< 30 \mu\text{m}$**
- x IKF-Frankfort+IPHC+IMEC
  - Adaptable to the support shape
    - Beam pipes, detector edges, ...

## ■ More “embedding”

- x Stitching sensors (proposed by several foundries)
  - reduce metal traces & support
- x Opto-couplers
  - High data-throughput with limited additional material

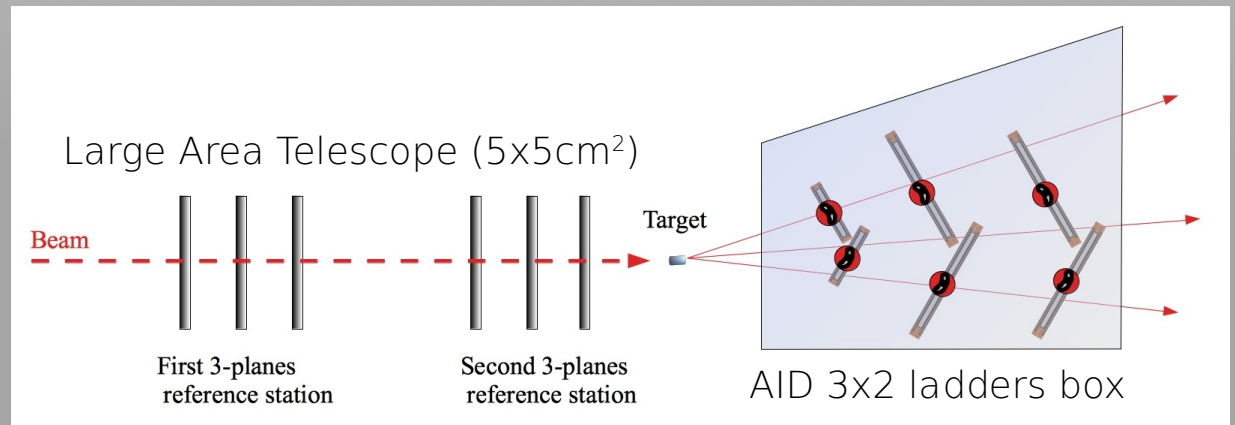


IMEC-Leuven, Belgium examples:



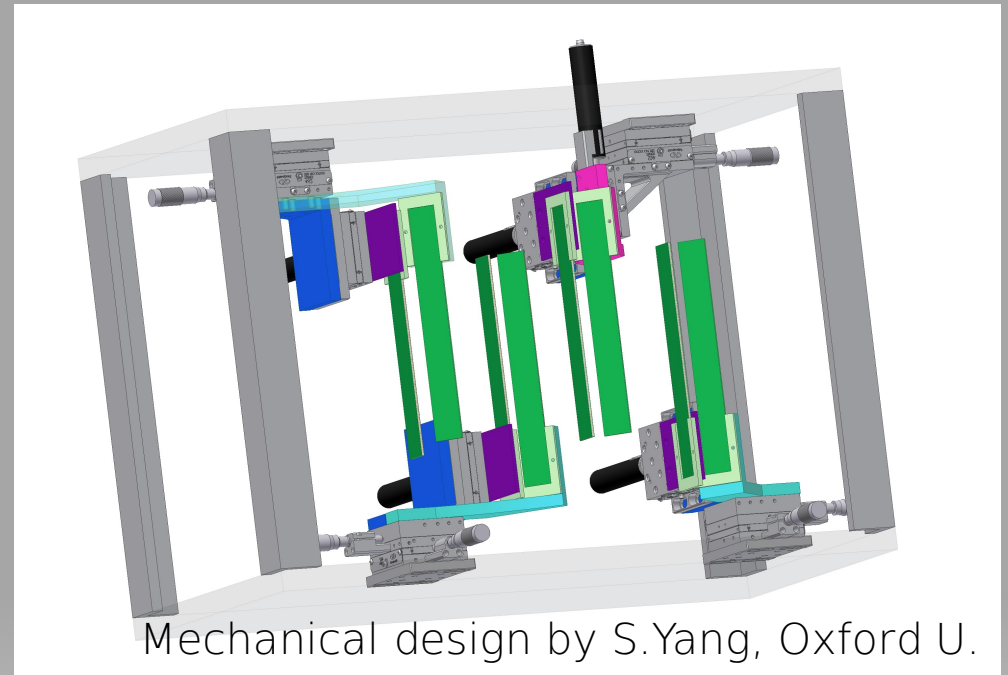


# Testing, evaluating



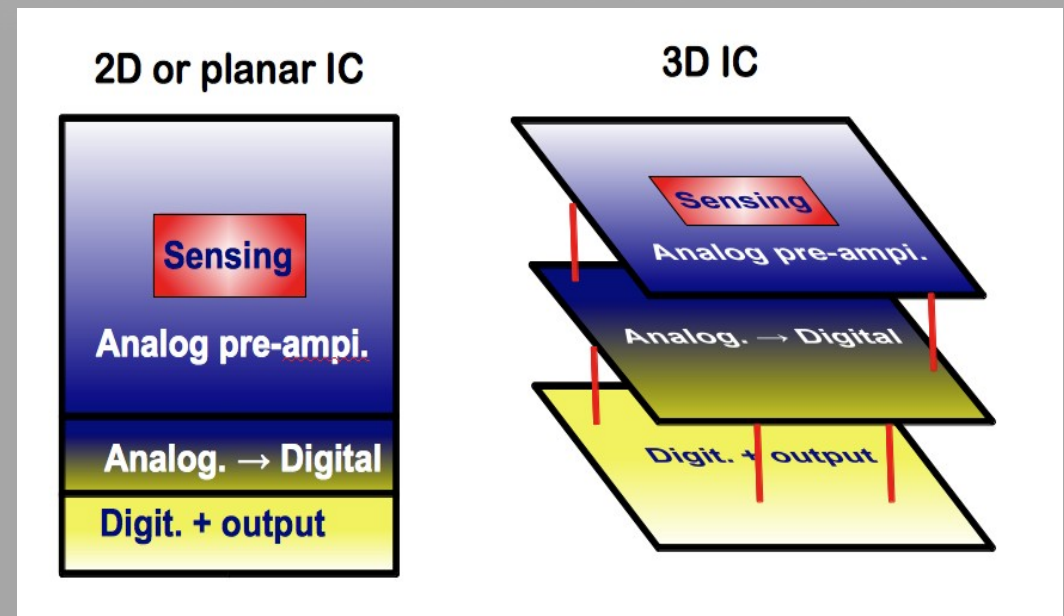
## ■ The AIDA project

- ✗ EU-FrameProg.7, 2011-2014
- ✗ Workpackage 9.2
  - Alignment studies
  - Power extraction
  - Mechanical stability
  - Power pulsing (ILC)



## ■ Combining functionalities & technologies

- x Best prepared for readout (optical link)
- x **Overcome 2D process limitations**
  - Smallest feature size
  - rad.tol. sensitive layer
  - Integrate more intelligence
  - Geometrically effective
- x Road to r.o. time  $\sim \mu\text{s}$  level



## ■ International 3D consortium

- x Lead by FNAL (pioneering work)
- x First circuits expected in 2010 (many different approaches)
- x More info on Thursday session
  - [G.Traversi](#), "3D consrtium", 9h
  - [R.Yarema](#) "The Via Revolution", 11h

- On the roads offered by different technologies for MAPS
- Challenge I: higher hit rate
  - x Deep sub-micron 2D processes,  $\sim 10\mu\text{s}$
  - x Advanced integration technologies: compact multi-layer systems
  - x Most promising: 3D processes,  $\sim \mu\text{s}$  read-out >2015
- Challenge II: higher radiation tolerance
  - x High resistivity epitaxial layer for non-ionizing rad.
- System challenge: data transmission & storage bottleneck
  - x Advanced integration
- Impact on imaging systems
  - x From multi-layers & data throughput
  - x Intelligent imagers (definition, scene detection,...)
  - x Multi-type radiation detection (dosimetry, veto function,...)

Thanks for your attention



## ■ Acronyms helper

- x AID=Alignment Investigation Device
- x AIDA=Advanced European Infrastructures for Detectors at Accelerators
- x CBM=Compressed Baryonic Matter at FAIR, GSI
- x EUDET=EUropean DETector R&D towards the International Linear Collider
- x INMAPS=Isolated N-wells, or INtelligent MAPS
- x MALT=Monolithic Active Liquid Tranquillizer
- x MIMOSA=Minimum Ionizing MOS Active pixels sensor
- x PLUME=Pixelated Ladder with Ultra-low Material Embedding
- x SERWIETE=SEnsor Row Wrapped In Extra-Thin Envelope
- x STAR=Solenoid Tracker At Rhic, BNL